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December 2013

FQP7N80C / FQPF7N80C

N-Channel QFET® MOSFET

800 V, 6.6 A, 1.9 Ω

Description

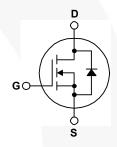
This N-Channel enhancement mode power MOSFET is • 6.6 A, 800 V, $R_{DS(on)}$ = 1.9 Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 27 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 10 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_D = 3.3 A$







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP7N80C	FQPF7N80C	Unit
V_{DSS}	Drain-Source Voltage		800		V
I _D	Drain Current - Continuous (T _C = 25°C)		6.6	6.6 *	Α
	- Continuous (T _C = 100°C)	Ī	4.2	4.2 *	Α
I _{DM}	Drain Current - Pulsed	Note 1)	26.4	26.4 *	Α
V _{GSS}	Gate-Source Voltage	± 30		V	
E _{AS}	Single Pulsed Avalanche Energy (Note		580		mJ
I _{AR}	Avalanche Current	Note 1)	6.6		Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		16.7		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5		V/ns
P _D	Power Dissipation (T _C = 25°C)		167	56	W
	- Derate above 25°C	1.33	0.44	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300		°C	

^{*} Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FQP7N80C	FQPF7N80C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.75	2.25	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ, Max.	0.5		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP7N80C	FQP7N80C	TO-220	Tube	N/A	N/A	50 units
FQPF7N80C	FQPF7N80C	TO-220F	Tube	N/A	N/A	50 units

Flactrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	800			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.93		V/°C
I _{DSS} Zero Gate	Zana Oata Valtana Brain Ourrant	V _{DS} = 800 V, V _{GS} = 0 V			10	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 640 V, T _C = 125°C			100	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 3.3 A		1.57	1.9	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 3.3 A		5.5		S
Dynam C _{iss}	ic Characteristics Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		1290	1680	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		120	155	pF
C _{rss}	Reverse Transfer Capacitance			10	13	pF
	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 400 \text{ V}, I_D = 6.6 \text{ A},$		35	80	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		100	210	ns
t _{d(off)}	Turn-Off Delay Time	(Note 4)		50	110	ns
t _f	Turn-Off Fall Time	, ,		60	130	ns
Q _g	Total Gate Charge	$V_{DS} = 640 \text{ V}, I_{D} = 6.6 \text{ A},$		27	35	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V	/	8.2		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	-	11		nC
	Sauras Diada Charastariatica a	nd Maximum Ratings				
Drain-S	Source Diode Characteristics a	ia maximam ratingo				
	Maximum Continuous Drain-Source Did				6.6	Α
Is		ode Forward Current			6.6 26.4	A A
I _S	Maximum Continuous Drain-Source Dic	ode Forward Current				
Is	Maximum Continuous Drain-Source Dick Maximum Pulsed Drain-Source Diode F	ode Forward Current Forward Current			26.4	Α

^{1.} Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 25 mH, I $_{AS}$ = 6.6 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C. 3.I $_{SD}$ \leq 8 A, di/dt \leq 200 A/ μ s , V $_{DD}$ \leq BV $_{DSS}$, starting T $_{J}$ = 25°C.

^{4.} Essentially independent of operating temperature.

Typical Characteristics

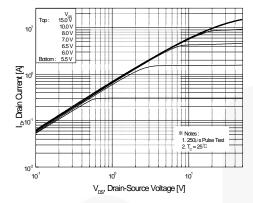


Figure 1. On-Region Characteristics

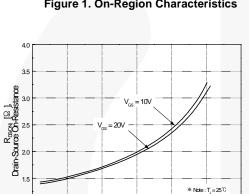


Figure 3. On-Resistance Variation vs **Drain Current and Gate Voltage**

I_D, Drain Current [A]

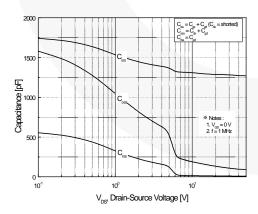


Figure 5. Capacitance Characteristics

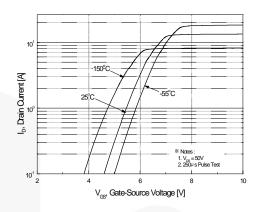


Figure 2. Transfer Characteristics

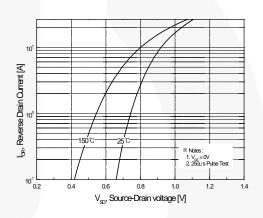


Figure 4. Body Diode Forward Voltage **Variation with Source Current** and Temperature

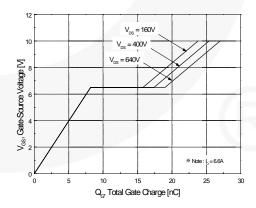


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

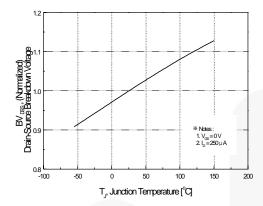


Figure 7. Breakdown Voltage Variation vs Temperature

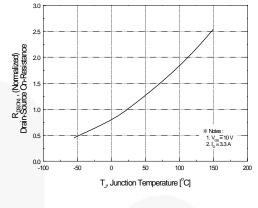


Figure 8. On-Resistance Variation vs Temperature

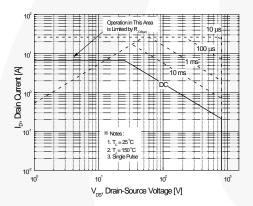


Figure 9-1. Maximum Safe Operating Area for FQP7N80C

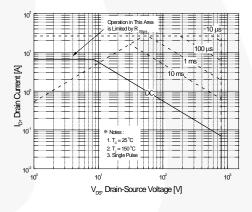


Figure 9-2. Maximum Safe Operating Area for FQPF7N80C

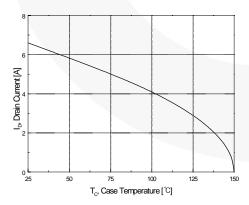


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

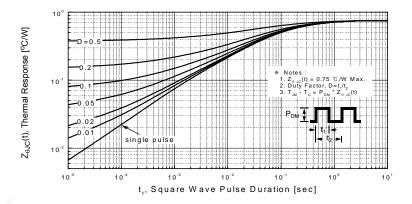


Figure 11-1. Transient Thermal Response Curve for FQP7N80C

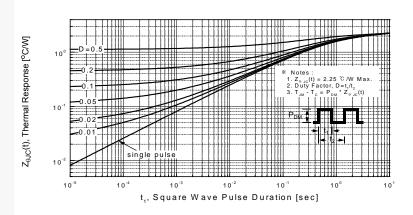


Figure 11-2. Transient Thermal Response Curve for FQPF7N80C

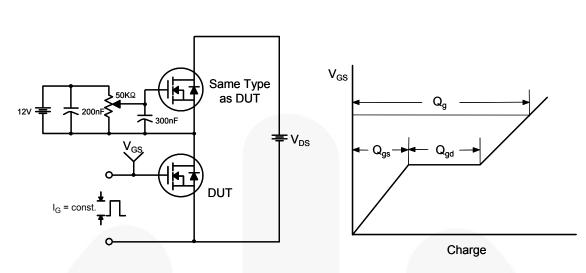


Figure 12. Gate Charge Test Circuit & Waveform

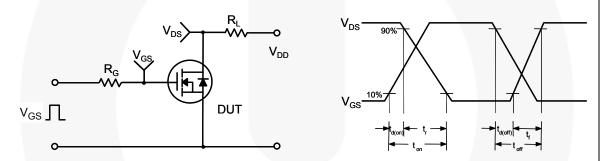


Figure 13. Resistive Switching Test Circuit & Waveforms

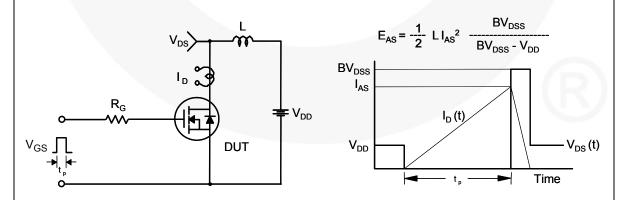
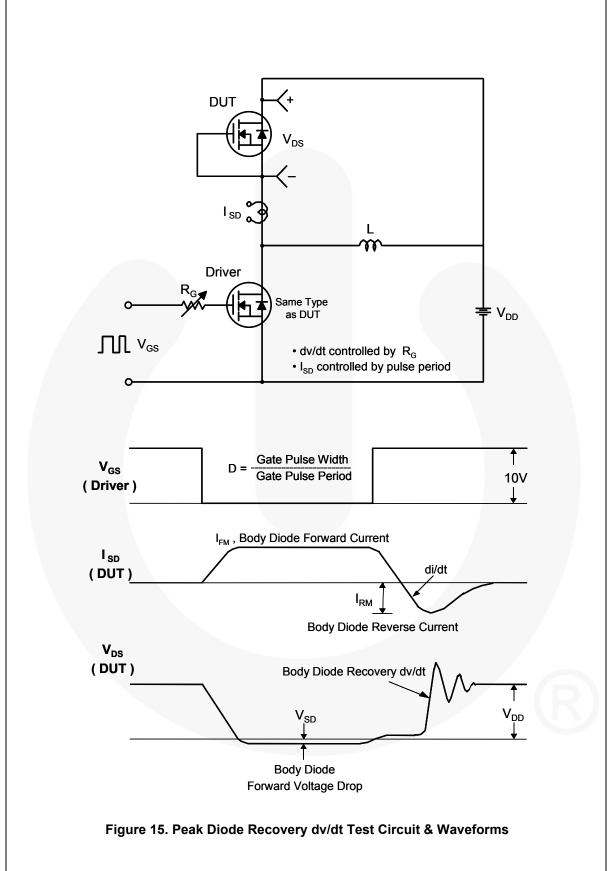


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

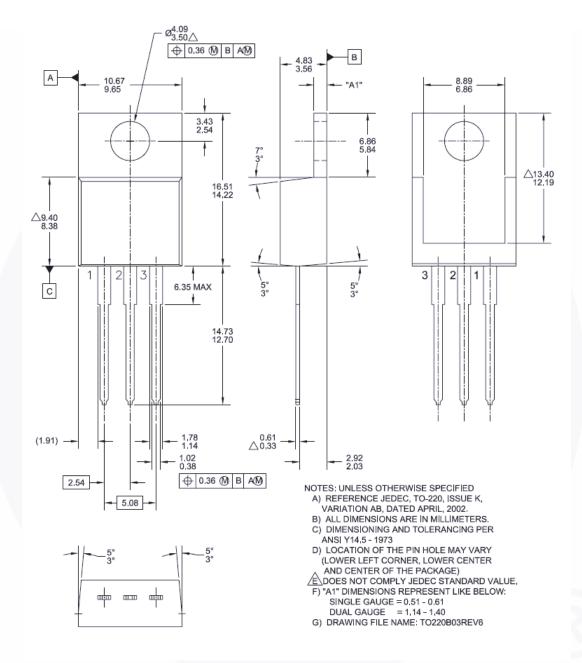


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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Mechanical Dimensions

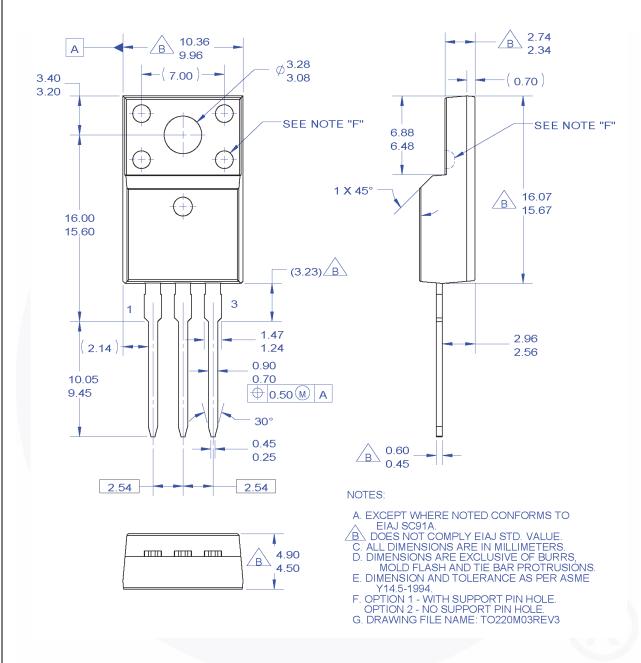


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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